

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1815	(257/327-329).ccls. and @ad<"20031205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/13 10:46
L2	924	(257/341).ccls. and @ad<"20031205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/13 10:51
L3	1256	(257/368).ccls. and @ad<"20031205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/13 10:59
L9	122	(257/502).ccls. and @ad<"20031205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/13 11:09
L11	649	(257/508 or 257/520).ccls. and @ad<"20031205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/13 11:29
L12	391	(257/621).ccls. and @ad<"20031205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/13 11:41
L13	76	semiconductor and (MOSFET or MOS or FET or IGBT or bipolar) and (((height) near5 substrate) with (total or entire or all)) and @ad<"20031205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/13 11:43
L15	1422	semiconductor and (MOSFET or MOS or FET or IGBT or bipolar) and (((length or thickness) near5 substrate) with (total or entire or all)) and @ad<"20031205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/13 11:46